

Si Photo-diode Chip—TKG060PDN

1. Scope

- The specification applies to PIN silicon photo-diode chips.
- Type : TKG060PDN.

2. Structure

- PIN planar type.
- Electrode topside (anode) : Aluminum.
backside (cathode) : Gold alloy.

3. Size

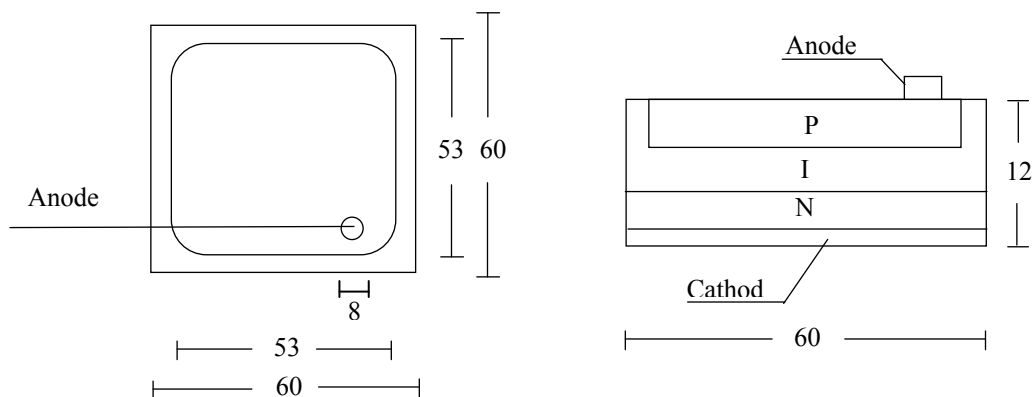
- Chip size : 60mil × 60mil (1.52mm × 1.52mm)
- Thickness : 12mil (0.30mm)
- Active area : 53mil × 53mil (1.35mm × 1.35mm)
- Pattern drawing : per fig. 1

4. Electro-Optical Characteristics

(Ta = +25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit.
Forward Voltage	V_F	$I_F=10\text{mA}$, $H=0$	0.5		1.3	V
Peak Sensitivity Wavelength	λ_p			550		nm
Spectral Response Range*	λ		470		620	nm
Reverse Dark Current	I_D	$V_R=10\text{V}$, $H=0$		2	10	nA
Reverse Breakdown Voltage	V_{BR}	$I_R=100\mu\text{A}$, $H=0$	35			V
Rise time/Fall time	T_r/T_f	$V_R=5\text{V}$, $R_L=50\Omega$			100	nS

*Spectral Range at Visible Light Range



Unit : mil

fig. 1

2012.May



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